

# NRTSV30H120CT

## Low Forward Voltage Trench-based Schottky Rectifier

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

### Mechanical Characteristics

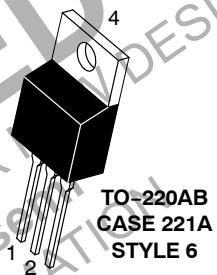
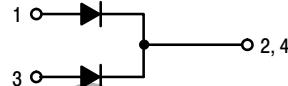
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



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### PIN CONNECTIONS



### MARKING DIAGRAM



TS30H120G = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

AKA = Polarity Designator

G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# NRTSV30H120CT

## MAXIMUM RATINGS

| Rating  | Symbol                                 | Value       | Unit |
|---|--|-------------|------|
| Peak Repetitive Reverse Voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage  | $V_{RRM}$<br>$V_{RWM}$<br>$V_R$        | 120         | V    |
| Average Rectified Forward Current<br>(Rated $V_R$ , $T_C = 124^\circ\text{C}$ )<br>(Rated $V_R$ , $T_C = 134^\circ\text{C}$ )   | $I_{F(AV)}$<br>Per device<br>Per diode | 30<br>15    | A    |
| Peak Repetitive Forward Current<br>(Rated $V_R$ , Square Wave, 20 kHz, $T_C = 119^\circ\text{C}$ )<br>(Rated $V_R$ , Square Wave, 20 kHz, $T_C = 132^\circ\text{C}$ ) | $I_{FRM}$<br>Per device<br>Per diode   | 60<br>30    | A    |
| Nonrepetitive Peak Surge Current<br>(Surge applied at rated load conditions halfwave, single phase, 60 Hz)  | $I_{FSM}$                              | 125         | A    |
| Operating Junction Temperature  | $T_J$                                  | -55 to +150 | °C   |
| Storage Temperature   | $T_{stg}$                              | -55 to +150 | °C   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

| Rating  | Symbol                             | Value       | Unit         |
|---|------------------------------------|-------------|--------------|
| Maximum Thermal Resistance per Device (Note 1)<br>Junction-to-Case<br>Junction-to-Ambient | $R_{\theta JC}$<br>$R_{\theta JA}$ | 1.0<br>69.3 | °C/W<br>°C/W |

1. Assumes 150 mm<sup>2</sup> 1 oz. copper bond pad, on a FR4 board.

## ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

| Rating   | Symbol | Typ                              | Max                        | Unit                     |
|--|--------|----------------------------------|----------------------------|--------------------------|
| Maximum Instantaneous Forward Voltage (Note 2)<br>( $I_F = 7.5 \text{ A}$ , $T_J = 25^\circ\text{C}$ )<br>( $I_F = 15 \text{ A}$ , $T_J = 25^\circ\text{C}$ )<br><br>( $I_F = 7.5 \text{ A}$ , $T_J = 125^\circ\text{C}$ )<br>( $I_F = 15 \text{ A}$ , $T_J = 125^\circ\text{C}$ ) | $V_F$  | 0.65<br>0.87<br><br>0.56<br>0.66 | —<br>0.93<br><br>—<br>0.70 | V                        |
| Maximum Instantaneous Reverse Current (Note 2)<br>( $V_R = 90 \text{ V}$ , $T_J = 25^\circ\text{C}$ )<br>( $V_R = 90 \text{ V}$ , $T_J = 125^\circ\text{C}$ )<br><br>(Rated dc Voltage, $T_J = 25^\circ\text{C}$ )<br>(Rated dc Voltage, $T_J = 125^\circ\text{C}$ )               | $I_R$  | 3.8<br>4.3<br><br>8.6<br>7.2     | 35<br>15                   | μA<br>mA<br><br>μA<br>mA |
| Diode Capacitance<br>(Rated dc Voltage, $T_J = 25^\circ\text{C}$ )   | $C_d$  | 95                               | —                          | pF                       |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

## ORDERING INFORMATION

| Device         | Package               | Shipping        |
|----------------|-----------------------|-----------------|
| NRTSV30H120CTG | TO-220AB<br>(Pb-Free) | 50 Units / Rail |

## TYPICAL CHARACTERISTICS

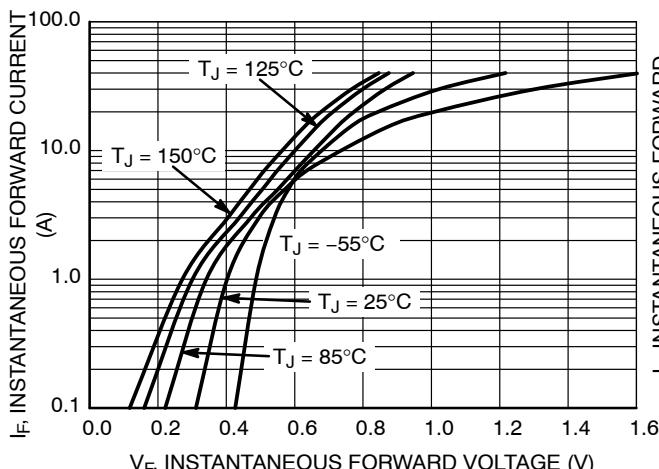


Figure 1. Typical Instantaneous Forward Characteristics

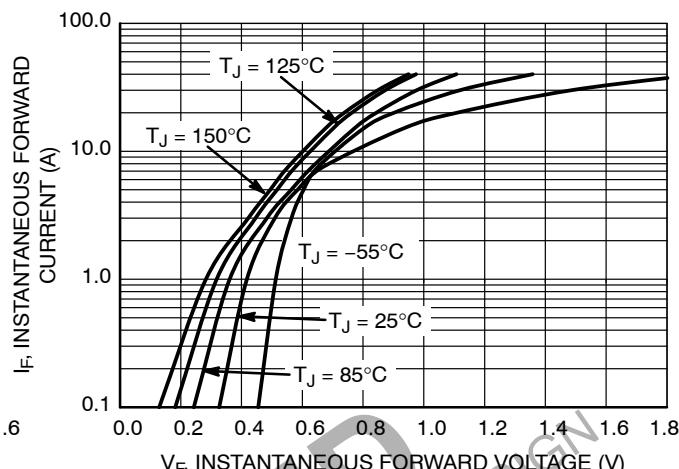


Figure 2. Maximum Instantaneous Forward Characteristics

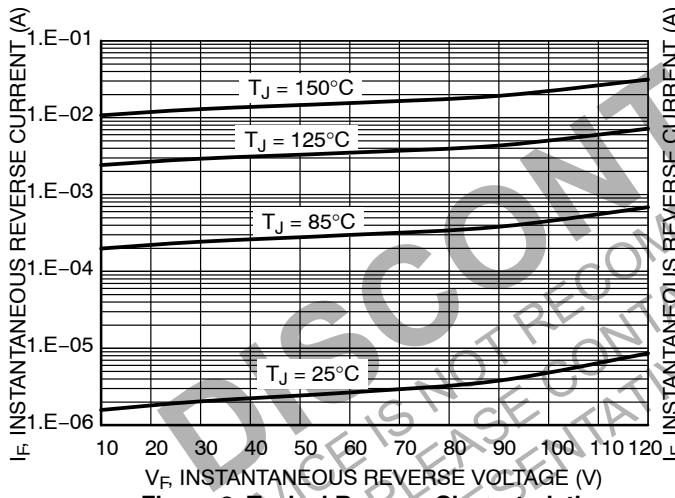


Figure 3. Typical Reverse Characteristics

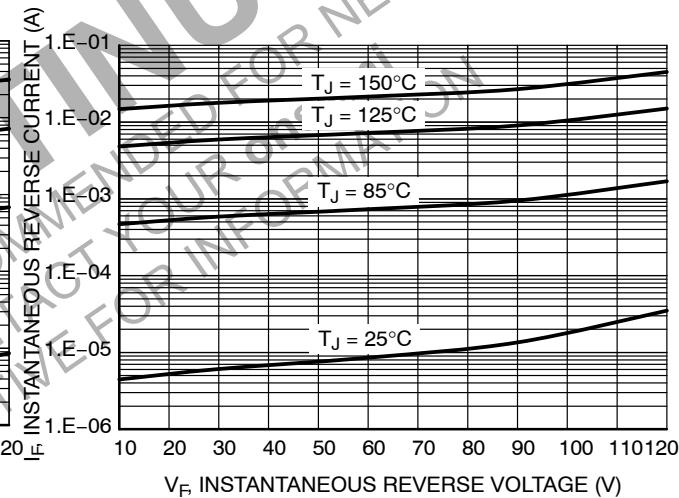


Figure 4. Maximum Reverse Characteristics

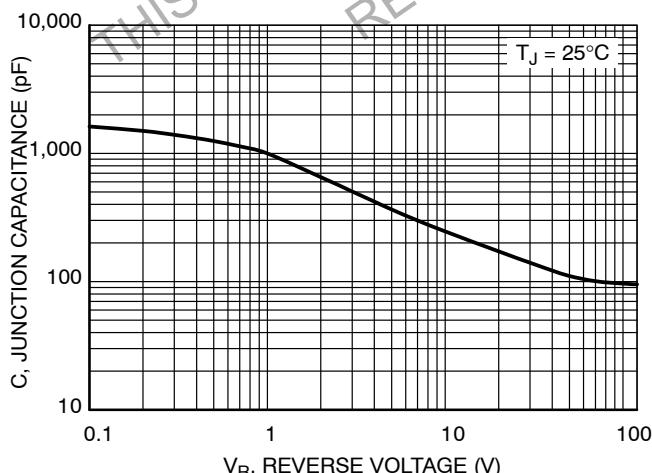


Figure 5. Typical Junction Capacitance

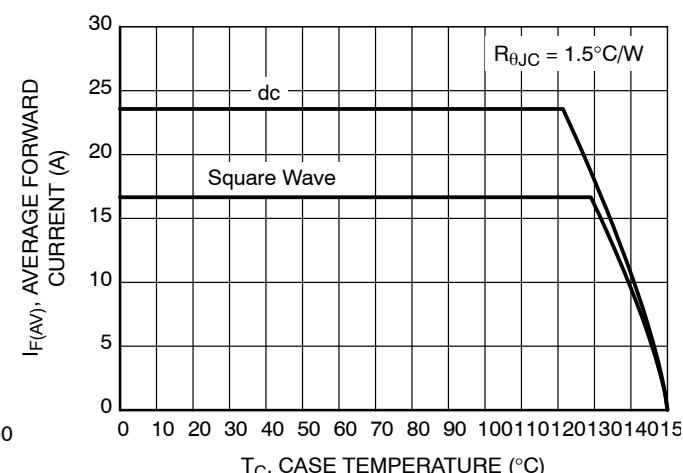


Figure 6. Current Derating per Leg

# NRTSV30H120CT

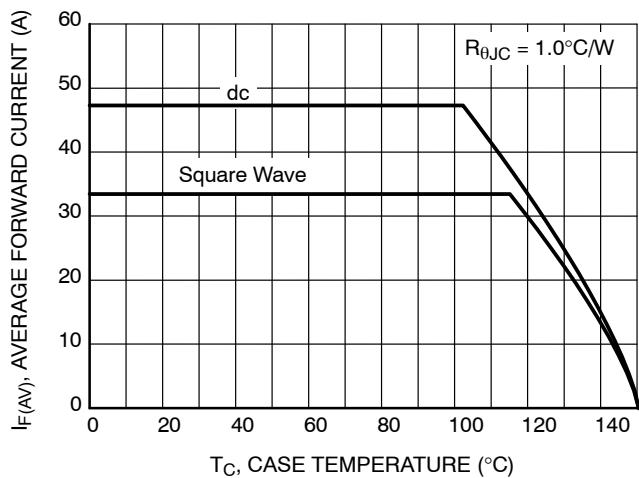


Figure 7. Current Derating, per Device

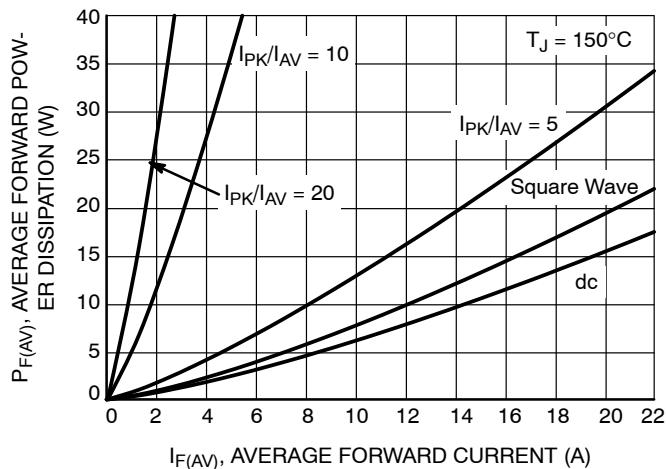


Figure 8. Forward Power Dissipation

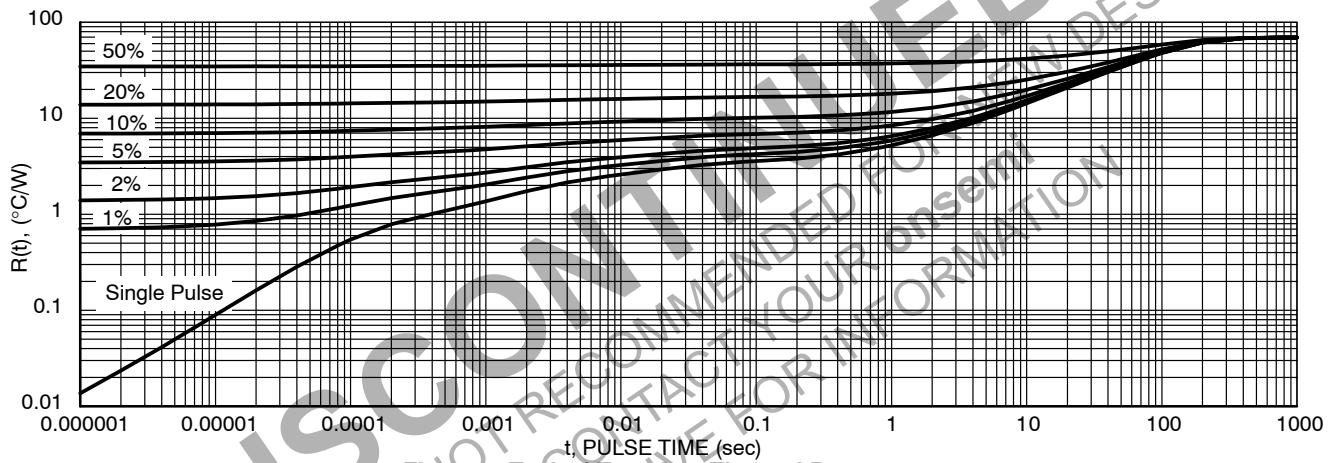
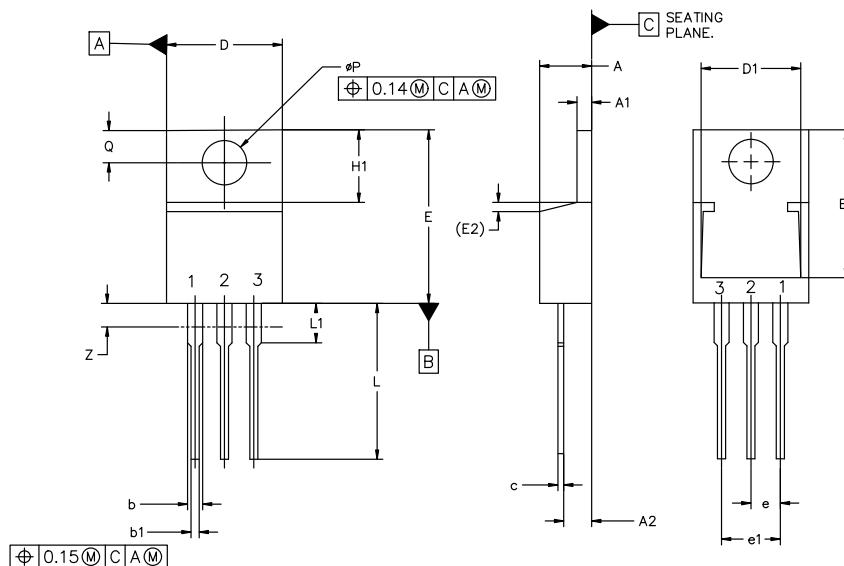


Figure 9. Typical Transient Thermal Response


**TO-220-3 10.10x15.12x4.45, 2.54P**  
CASE 221A  
ISSUE AL

DATE 05 FEB 2025



| MILLIMETERS |          |       |       |
|-------------|----------|-------|-------|
| DIM         | MIN      | NOM   | MAX   |
| A           | 4.07     | 4.45  | 4.83  |
| A1          | 1.15     | 1.28  | 1.41  |
| A2          | 2.04     | 2.42  | 2.79  |
| b           | 1.15     | 1.34  | 1.52  |
| b1          | 0.64     | 0.80  | 0.96  |
| c           | 0.36     | 0.49  | 0.61  |
| D           | 9.66     | 10.10 | 10.53 |
| D1          | 8.43     | 8.63  | 8.83  |
| E           | 14.48    | 15.12 | 15.75 |
| E1          | 12.58    | 12.78 | 12.98 |
| E2          | 1.27 REF |       |       |

| MILLIMETERS |       |       |       |
|-------------|-------|-------|-------|
| DIM         | MIN   | NOM   | MAX   |
| e           | 2.42  | 2.54  | 2.66  |
| e1          | 4.83  | 5.08  | 5.33  |
| H1          | 5.97  | 6.22  | 6.47  |
| L           | 12.70 | 13.49 | 14.27 |
| L1          | 2.80  | 3.45  | 4.10  |
| Q           | 2.54  | 2.79  | 3.04  |
| øP          | 3.60  | 3.85  | 4.09  |
| Z           | ---   | ---   | 3.48  |

## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRRREGULARITIES ARE ALLOWED.

STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. Emitter  
4. COLLECTOR

STYLE 2:  
PIN 1. BASE  
2. Emitter  
3. COLLECTOR  
4. Emitter

STYLE 3:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 4:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

STYLE 5:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 6:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 7:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 8:  
PIN 1. CATHODE  
2. ANODE  
3. EXTERNAL TRIP/DELAY  
4. ANODE

STYLE 9:  
PIN 1. GATE  
2. COLLECTOR  
3. Emitter  
4. COLLECTOR

STYLE 10:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN  
4. SOURCE

STYLE 11:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE  
4. SOURCE

STYLE 12:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. NOT CONNECTED

|                  |                                  |   |
|------------------|----------------------------------|---|
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| DESCRIPTION:     | TO-220-3 10.10x15.12x4.45, 2.54P | PAGE 1 OF 1   |

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